

2N5550

Amplifier Transistor

- Collector-Emitter Voltage: V_{CEO}= 140V
 Collector Dissipation: P_C (max)=625mW



1. Emitter 2. Base 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	160	V	
V _{CEO}	Collector-Emitter Voltage	140	V	
V _{EBO}	Emitter-Base Voltage	6	V	
I _C	Collector Current	600	mA	
P _C	Collector Dissipation	625	mW	
T _J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	-55 ~ 150	°C	

Refer to 2N5551 for graphs

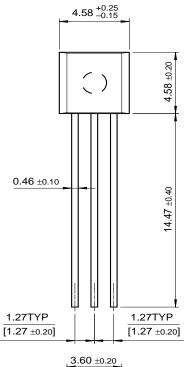
Electrical Characteristics T_a=25°C unless otherwise noted

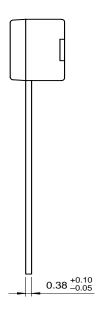
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =100μA, I _E =0	160			V
BV _{CEO}	* Collector-Emitter Breakdown Voltage	I _C =1mA, I _B =0	140			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =10μA, I _C =0	6			V
I _{CBO}	Collector Cut-off Current	V _{CB} =100V, I _E =0			100	nA
I _{EBO}	Emitter Cut-off Current	V _{EB} = 4V, I _C =0			50	nA
h _{FE}	* DC Current Gain	I_{C} =1mA, V_{CE} =5V I_{C} =10mA, V_{CE} =5V I_{C} =50mA, V_{CE} =5V	60 60 20		250	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C =10mA, I _B =1mA I _C =50mA, I _B =5mA			0.15 0.25	V V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C =10mA, I _B =1mA I _C =50mA, I _B =5mA			1 1.2	V V
f _T	Current Gain Bandwidth Product	I _C =10mA, V _{CE} =10V, f=100MHz	100		300	MHz
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=1MHz			6	pF
NF	Noise Figure	I_C =250μA, V_{CE} =5V R_S =1K Ω f=10Hz to 15.7KHz			10	dB

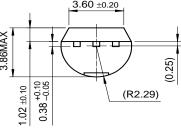
^{*} Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Package Demensions

TO-92







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